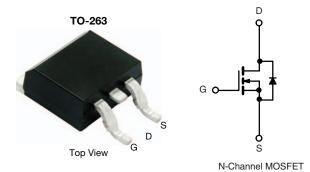


Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0059				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0080				
I _D (A)	75				
Configuration	Single				
Package	TO-263				



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	
Gate-Source Voltage	V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C a		75	
	T _C = 125 °C	I _D	67	А
Continuous Source Current (Diode Conduct	ion) ^a	I _S	75	
Pulsed Drain Current b		I _{DM}	180	
Single Pulse Avalanche Current	1 0111	I _{AS}	60	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	180	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	Б	166	10/
	T _C = 125 °C	P_{D}	55	W
Operating Junction and Storage Temperature Range		T _J , T _{stq}	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB mount c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)		R_{thJC}	0.9	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					L	L		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		100	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	500		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 30 A	-	0.0046	6 0.0059		
	Б	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0099	Ω	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0123		
		V _{GS} = 4.5 V	= 4.5 V I _D = 20 A		0.0056	0.0080		
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 25 A		-	95	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}				4170	5500		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	1935	2600	pF	
Reverse Transfer Capacitance	C _{rss}			-	160	220		
Total Gate Charge ^c	Qg			-	66	100		
Gate-Source Charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 50 \text{ A}$	-	14	-	nC	
Gate-Drain Charge ^c	Q_{gd}	1		-	12	-		
Gate Resistance	R_g	f = 1 MHz		0.90	1.92	3	Ω	
Turn-On Delay Time ^c	t _{d(on)}				13	25		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 1.08 \Omega$ $I_{D} \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	21	35		
Turn-Off Delay Time ^c	t _{d(off)}			-	34	60	ns	
Fall Time ^c	t _f			-	13	25		
Source-Drain Diode Ratings and Chara	acteristics b							
Pulsed Current ^a	I _{SM}			-	-	180	Α	
Forward Voltage	V_{SD}	$I_F = 50 \text{ A}, V_{GS} = 0$			0.90	1.5	V	

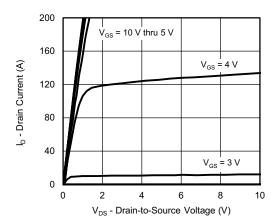
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

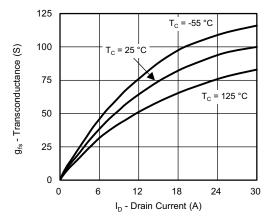
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



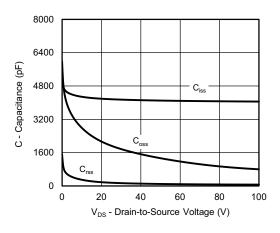
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



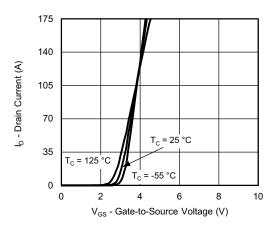
Output Characteristics



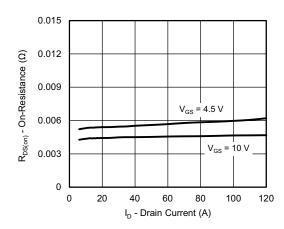
Transconductance



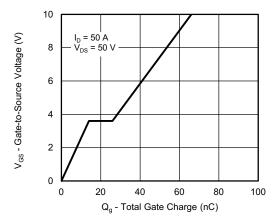
Capacitance



Transfer Characteristics



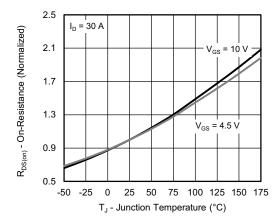
On-Resistance vs. Drain Current



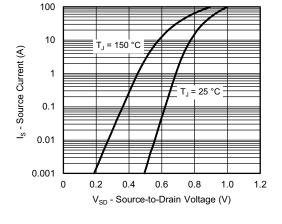
Gate Charge



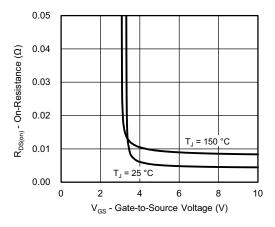
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



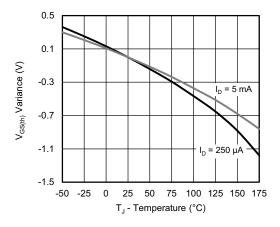
On-Resistance vs. Junction Temperature



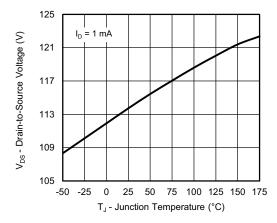
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



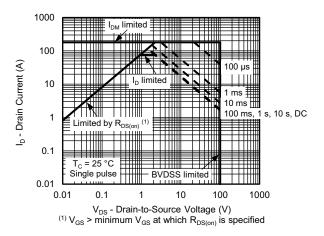
Threshold Voltage



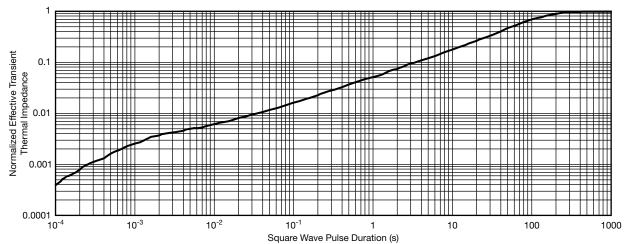
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



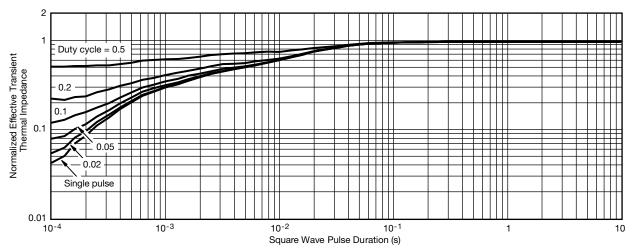
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

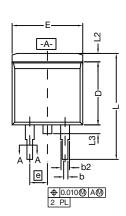
Note

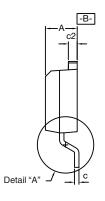
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

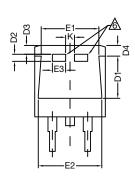
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TO-263 (D²PAK): 3-LEAD

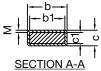








DETAIL A (ROTATED 90°)



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- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

	INCHES		MILLIN	METERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	- 0.002			0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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